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# NGTD30T120F2

## IGBT Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

### Features

- Extremely Efficient Trench with Field Stop Technology
- Low  $V_{CE(sat)}$  Loss Reduces System Power Dissipation

### Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^\circ\text{C}$	$V_{CE}$	1200	V
DC Collector Current, limited by $T_{J(max)}$	$I_C$	(Note 1)	A
Pulsed Collector Current (Note 2)	$I_{C, pulse}$	200	A
Gate–Emitter Voltage	$V_{GE}$	$\pm 20$	V
Maximum Junction Temperature	$T_J$	$-55$ to $+175$	$^\circ\text{C}$
Short Circuit Withstand Time, $V_{GE} = 15\text{ V}$ , $V_{CE} = 500\text{ V}$ , $T_J \leq 150^\circ\text{C}$	$T_{SC}$	10	$\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly.
2.  $T_{pulse}$  limited by  $T_{jmax}$ ; 10  $\mu\text{s}$  pulse,  $V_{GE} = 15\text{ V}$ .

### MECHANICAL DATA

Parameter	Value	Unit
Die Size	6241 x 4741	$\mu\text{m}^2$
Emitter Pad Size	See die layout	$\mu\text{m}^2$
Gate Pad Size	410 x 680	$\mu\text{m}^2$
Die Thickness	5	mils
Wafer Size	150	mm
Top Metal	5 $\mu\text{m}$ AlSi	
Back Metal	2 $\mu\text{m}$ TiNiAg	
Max possible chips per wafer	415	
Passivation frontside	Oxide–Nitride	
Reject ink dot size	25 mils	
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28 $^\circ\text{C}$ , 30–65%RH	Type: Die on tape in ring–pack Storage time: < 3 months	

### ORDERING INFORMATION

Device	Inking?	Shipping
NGTD30T120F2WP	Yes	Bare Wafer in Jar
NGTD30T120F2SWK	Yes	Sawn Wafer on Tape

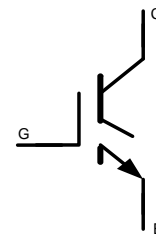


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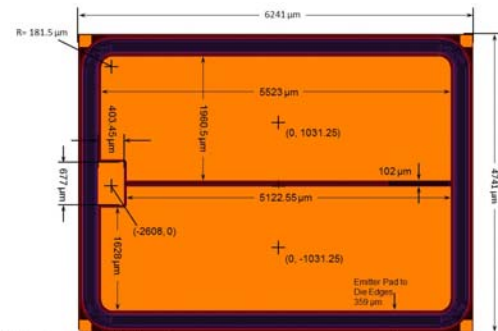
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$V_{RCE} = 1200\text{ V}$   
 $I_C = \text{Limited by } T_{J(max)}$

IGBT DIE



DIE OUTLINE



All dimensions in  $\mu\text{m}$  (with  $\pm 2\%$  tolerance)  
Die dimensions do not include 100 $\mu\text{m}$  scribe grid  
Pad center coordinates relative to die center

# NGTD30T120F2

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

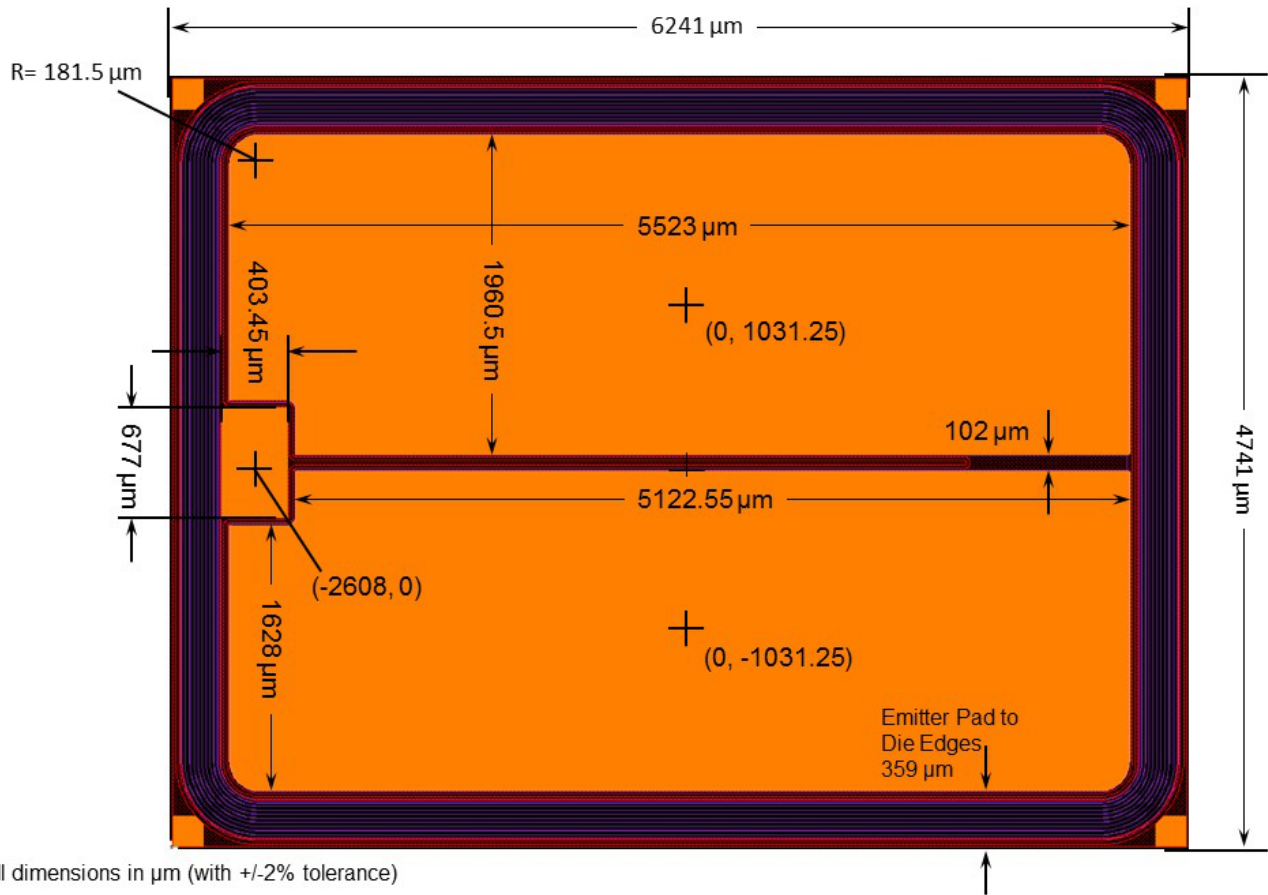
Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>STATIC CHARACTERISTICS</b>						
Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	1200			V
Collector-Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$	$V_{CE(sat)}$		2.0	2.4	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\ \mu\text{A}$	$V_{GE(TH)}$	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	$I_{CES}$			0.4	mA
Gate Leakage Current	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$			200	nA

## DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$		7385		pF
Output Capacitance		$C_{oes}$		230		pF
Reverse Transfer Capacitance		$C_{res}$		140		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## DIE LAYOUT



All dimensions in μm (with +/-2% tolerance)


Die dimensions do not include 100μm scribe grid

Pad center coordinates relative to die center

# NGTD30T120F2

## Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

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